



گروه فنی مهندسی جوش و برش مقدم

اعتماد از شما کیفیت و تخصص از ما



09153223758



051-37581400



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مشهد خیام شمالی 63 خیابان پردیس 3

برای کسب اطلاعات بیشتر بر روی لینک ها کلیک کنید

- 7 سال سابقه آموزش تعمیرات تخصصی دستگاه های جوش اینورتری تک فاز و 3 فاز
- 7 سال سابقه فروش قطعات الکترونیکی دستگاه جوش تک فاز و 3 فاز
- آموزش تخصصی تحلیل دستگاه های جوش اینورتری مختص ابراز فروشان
- آموزش تخصصی ابراز آلات شارژی

NGTB40N120IHLWG

IGBT

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Field Stop (FS) Trench construction, and provides superior performance in demanding switching applications, offering both low on-state voltage and minimal switching loss. The IGBT is well suited for resonant or soft switching applications. Incorporated

<http://onsemi.com>

into the device is a rugged co-packaged free wheeling diode with a low forward voltage.

Features

- Low Saturation Voltage using Trench with Field Stop Technology
- Low Switching Loss Reduces System Power Dissipation
- Optimized for Low Case Temperature in IH Cooker Application
- Low Gate Charge
- These are Pb-Free Devices

Typical Applications

- Inductive Heating
- Consumer Appliances
- Soft Switching

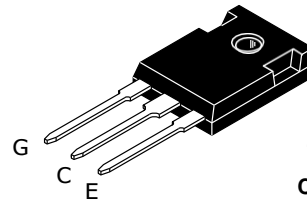
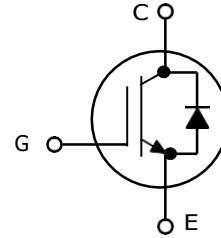
ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-emitter voltage	V_{CES}	1200	V
Collector current @ $T_c = 25^\circ\text{C}$ @ $T_c = 100^\circ\text{C}$	I_C	80 40	A
Pulsed collector current, T_{pulse} limited by $T_{J\text{max}}$	I_{CM}	320	A
Diode forward current @ $T_c = 25^\circ\text{C}$ @ $T_c = 100^\circ\text{C}$	I_F	80 40	A
Diode pulsed current, T_{pulse} limited by $T_{J\text{max}}$	I_{FM}	320	A
Gate-emitter voltage	V_{GE}	± 20	V
Power Dissipation @ $T_c = 25^\circ\text{C}$ @ $T_c = 100^\circ\text{C}$	P_D	260 104	W
Operating junction temperature range	T_J	-55 to +150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to +150	$^\circ\text{C}$
Lead temperature for soldering, 1/8" from case for 5 seconds	T_{SLD}	260	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

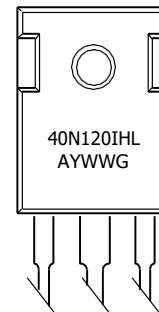
40 A, 1200 V

$V_{CE\text{sat}} = 1.90 \text{ V}$
 $E_{\text{off}} = 1.40 \text{ mJ}$



TO-247
CASE 340L
STYLE 4

MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
NGTB40N120IHLWG	TO-247 (Pb-Free)	30 Units / Rail

NGTB40N120IHLWG

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal resistance junction-to-case, for IGBT	$R_{\theta JC}$	0.48	$^{\circ}C/W$
Thermal resistance junction-to-case, for Diode	$R_{\theta JC}$	1.5	$^{\circ}C/W$
Thermal resistance junction-to-ambient	$R_{\theta JA}$	40	$^{\circ}C/W$

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise specified)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
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STATIC CHARACTERISTIC

Collector-emitter breakdown voltage, gate-emitter short-circuited	$V_{GE} = 0 V, I_C = 500 \mu A$	$V_{(BR)CES}$	1200	-	-	V
Collector-emitter saturation voltage	$V_{GE} = 15 V, I_C = 40 A$ $V_{GE} = 15 V, I_C = 40 A, T_J = 150^{\circ}C$	V_{CEsat}	-	1.90 2.1	2.35 -	V
Gate-emitter threshold voltage	$V_{GE} = V_{CE}, I_C = 400 \mu A$	$V_{GE(th)}$	4.5	5.5	6.5	V
Collector-emitter cut-off current, gate-emitter short-circuited	$V_{GE} = 0 V, V_{CE} = 1200 V$ $V_{GE} = 0 V, V_{CE} = 1200 V, T_J = 150^{\circ}C$	I_{CES}	-	-	0.5 2.0	mA
Gate leakage current, collector-emitter short-circuited	$V_{GE} = 20 V, V_{CE} = 0 V$	I_{GES}	-	-	200	nA

DYNAMIC CHARACTERISTIC

Input capacitance	$V_{CE} = 20 V, V_{GE} = 0 V, f = 1 MHz$	C_{ies}	-	10400	-	pF
Output capacitance		C_{oes}	-	245	-	
Reverse transfer capacitance		C_{res}	-	185	-	
Gate charge total	$V_{CE} = 600 V, I_C = 40 A, V_{GE} = 15 V$	Q_g		420		nC
Gate to emitter charge		Q_{ge}		95		
Gate to collector charge		Q_{gc}		178		

SWITCHING CHARACTERISTIC, INDUCTIVE LOAD

Turn-off delay time	$T_J = 25^{\circ}C$ $V_{CC} = 600 V, I_C = 40 A$ $R_g = 10 \Omega$	$t_{d(off)}$		360		ns
Fall time		t_f		130		
Turn-off switching loss		E_{off}		1.40		
Turn-off delay time	$T_J = 125^{\circ}C$ $V_{CC} = 600 V, I_C = 40 A$ $R_g = 10 \Omega$	$t_{d(off)}$		380		ns
Fall time		t_f		185		
Turn-off switching loss		E_{off}		2.6		

DIODE CHARACTERISTIC

Forward voltage	$V_{GE} = 0 V, I_F = 40 A$ $V_{GE} = 0 V, I_F = 40 A, T_J = 150^{\circ}C$	V_F		1.6 1.8	1.8	V
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NGTB40N120IHLWG

TYPICAL CHARACTERISTICS

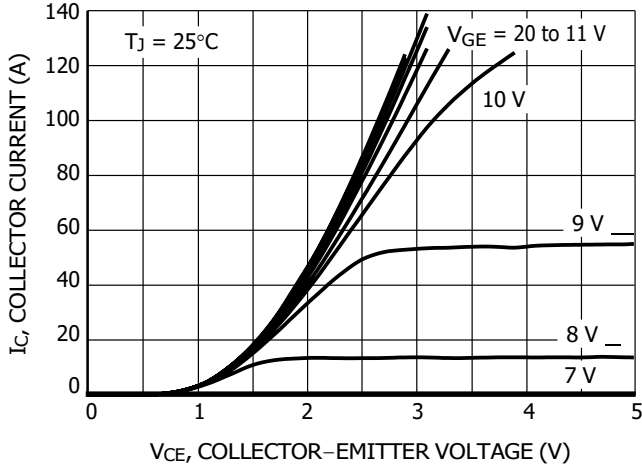


Figure 1. Output Characteristics

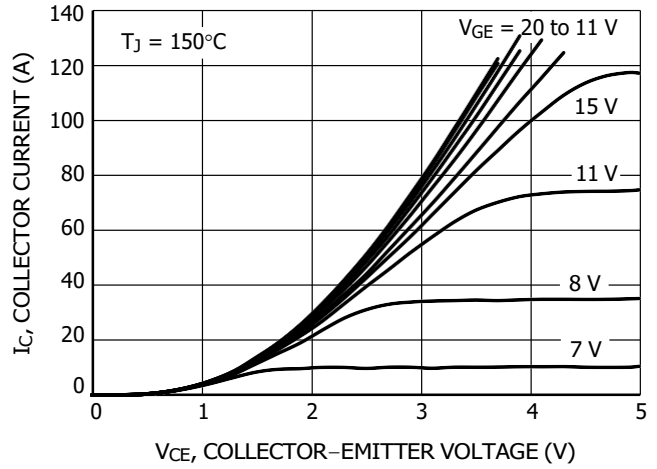


Figure 2. Output Characteristics

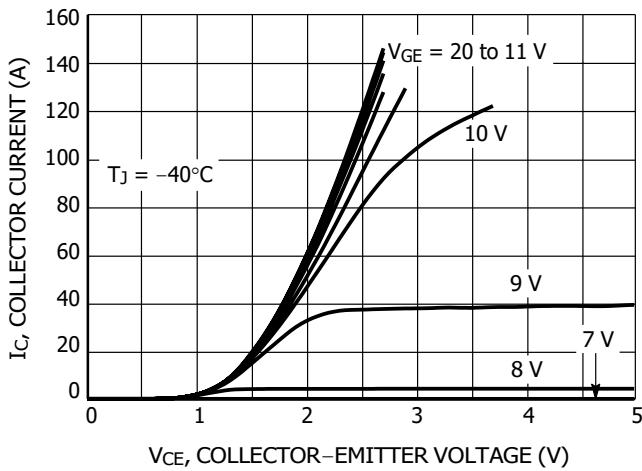


Figure 3. Output Characteristics

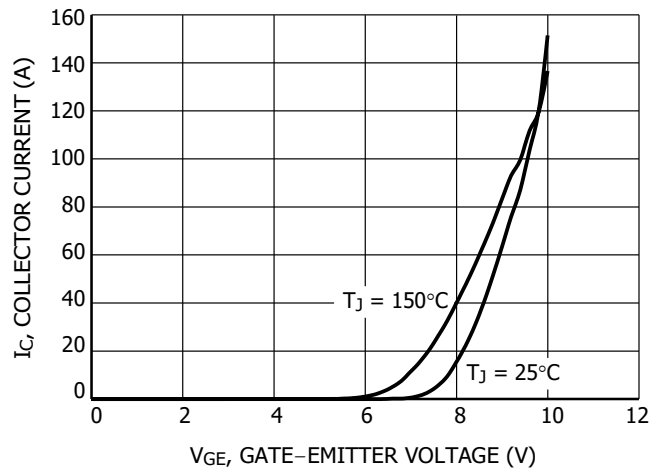


Figure 4. Typical Transfer Characteristics

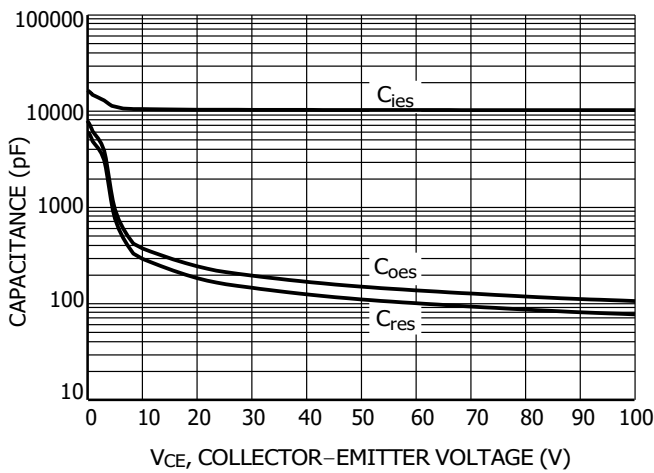


Figure 5. Typical Capacitance

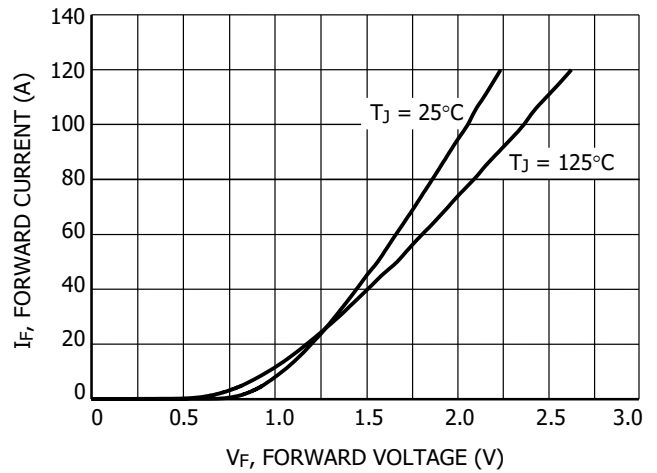


Figure 6. Diode Forward Characteristics

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TYPICAL CHARACTERISTICS

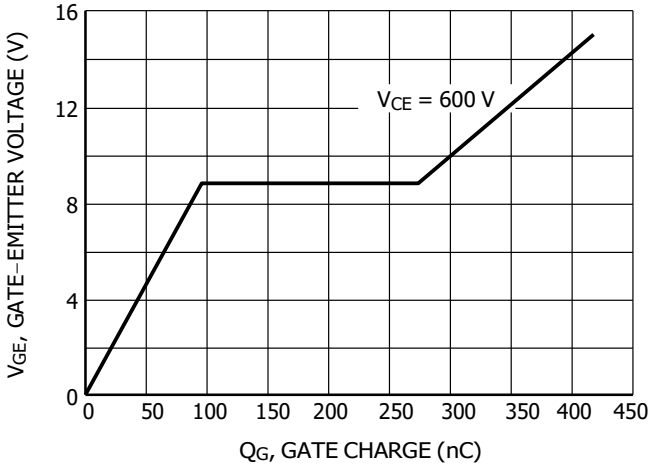


Figure 7. Typical Gate Charge

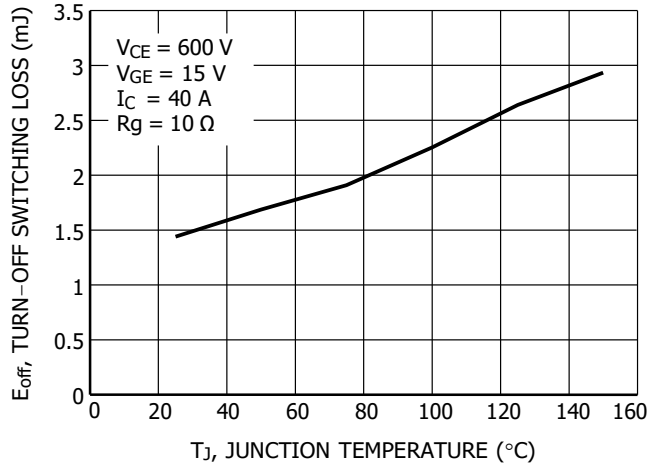


Figure 8. Energy Loss vs. Temperature

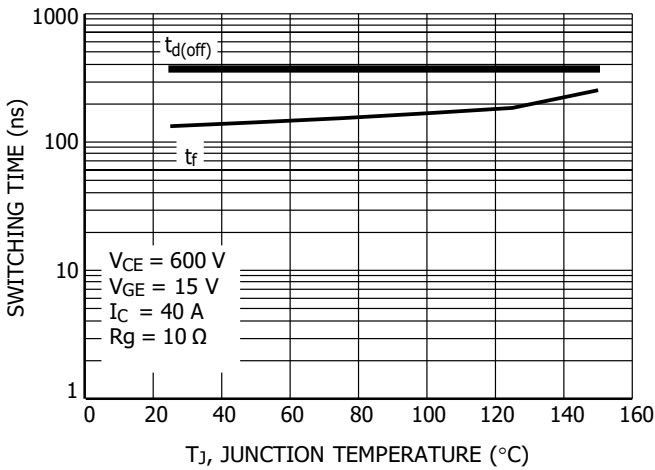


Figure 9. Switching Time vs. Temperature

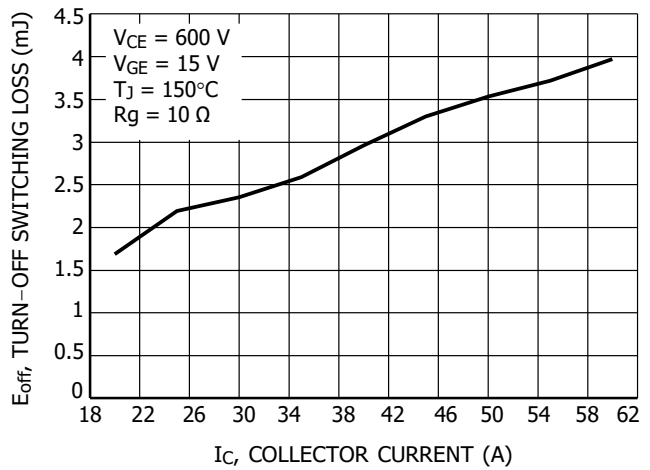


Figure 10. Energy Loss vs. I_C

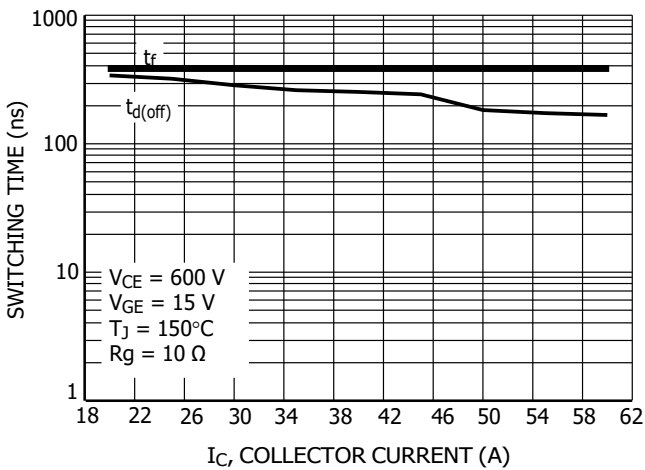


Figure 11. Switching Time vs. I_C

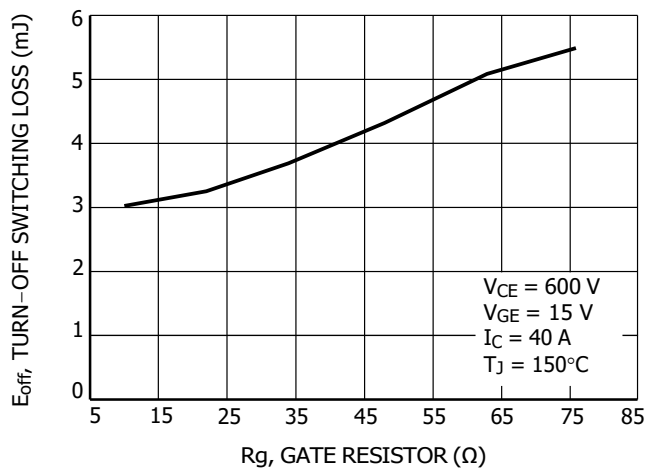


Figure 12. Energy Loss vs. R_g

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TYPICAL CHARACTERISTICS

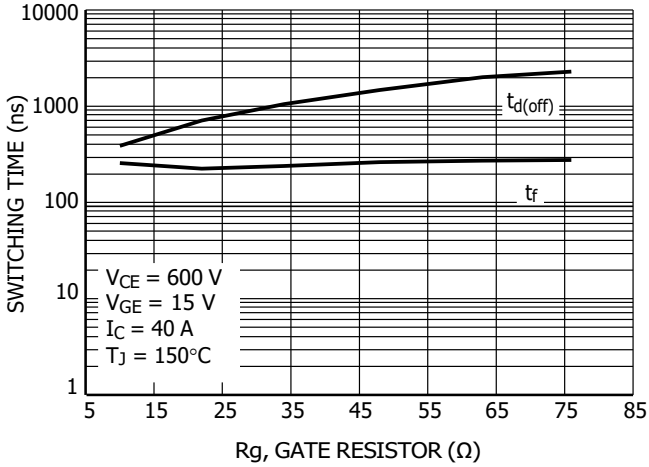


Figure 13. Switching Time vs. R_g

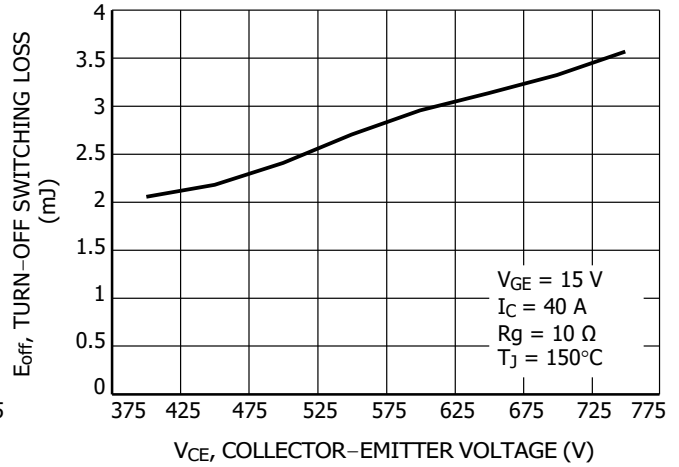


Figure 14. Energy Loss vs. V_{CE}

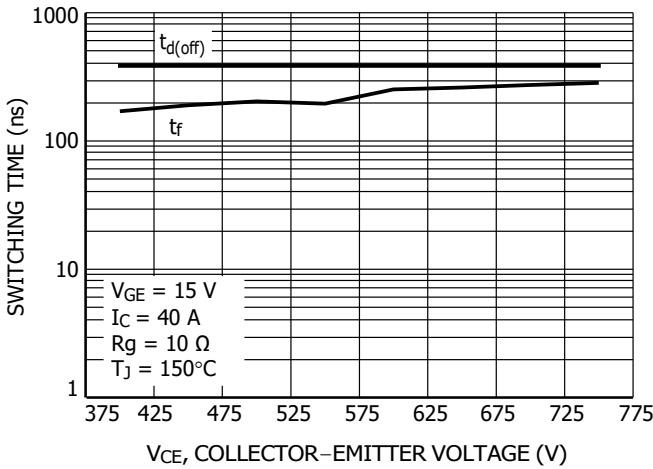


Figure 15. Switching Time vs. V_{CE}

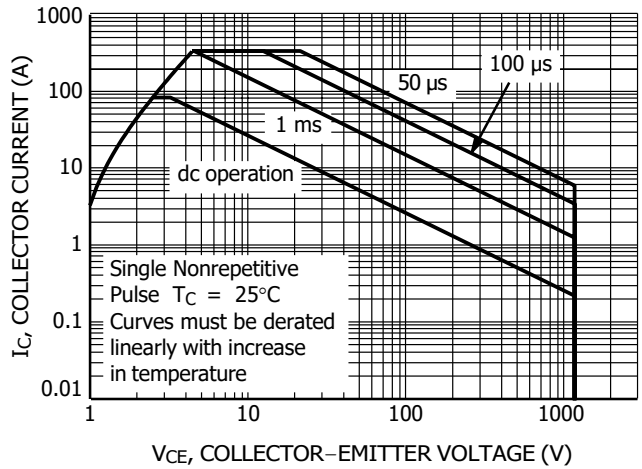


Figure 16. Safe Operating Area

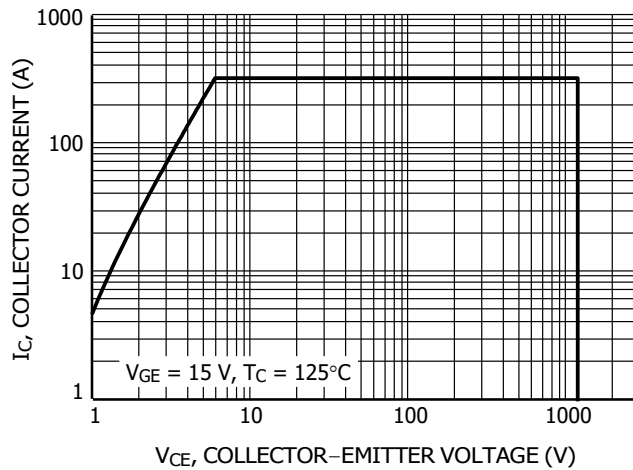


Figure 17. Reverse Bias Safe Operating Area

NGTB40N120HLWG

TYPICAL CHARACTERISTICS

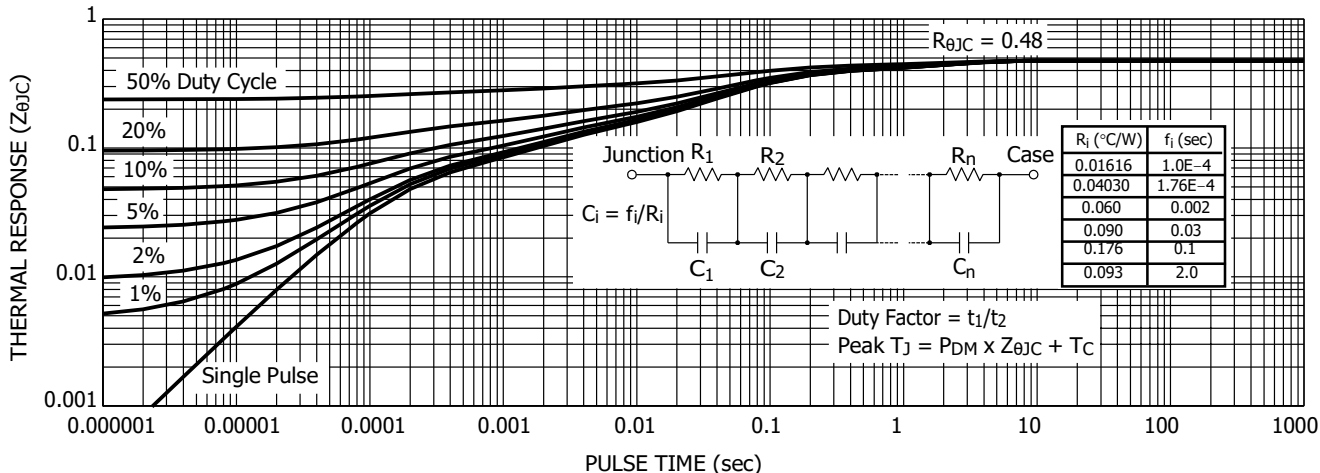


Figure 18. IGBT Transient Thermal Impedance

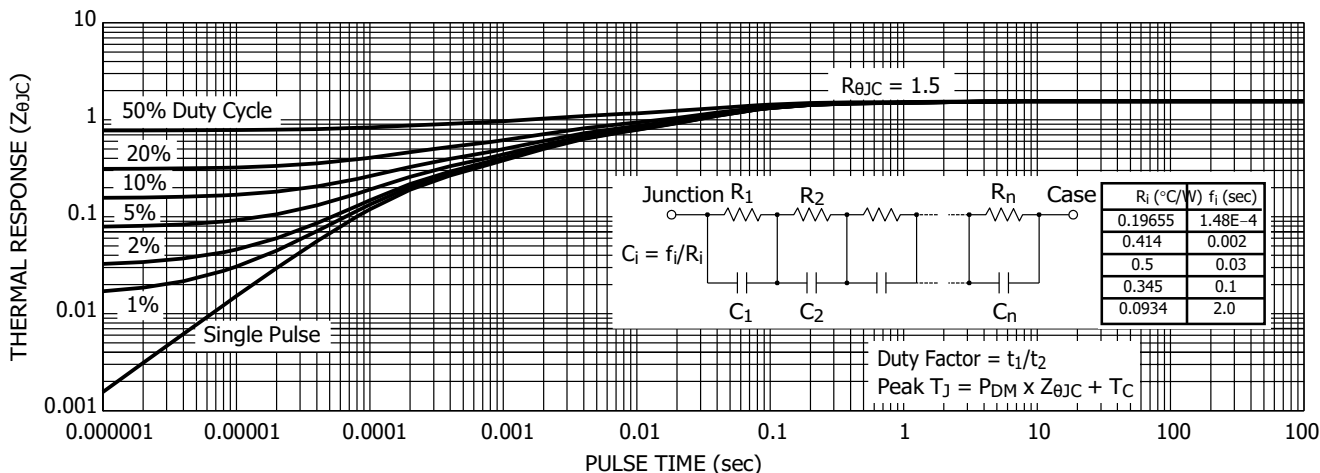


Figure 19. Diode Transient Thermal Impedance

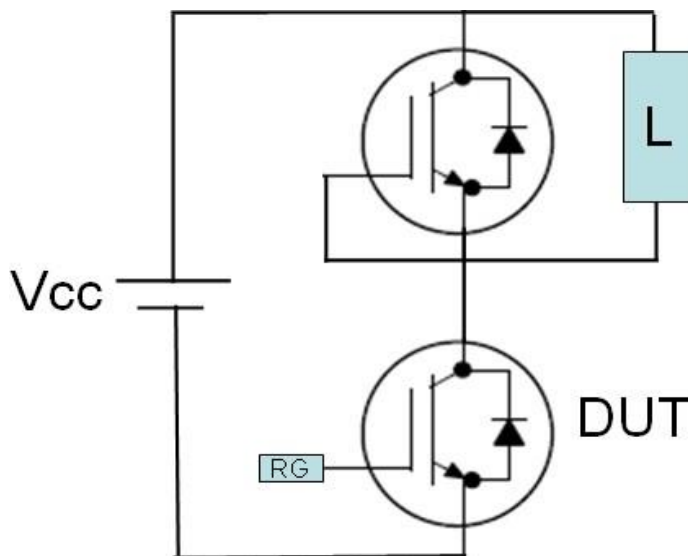


Figure 20. Test Circuit for Switching Characteristics

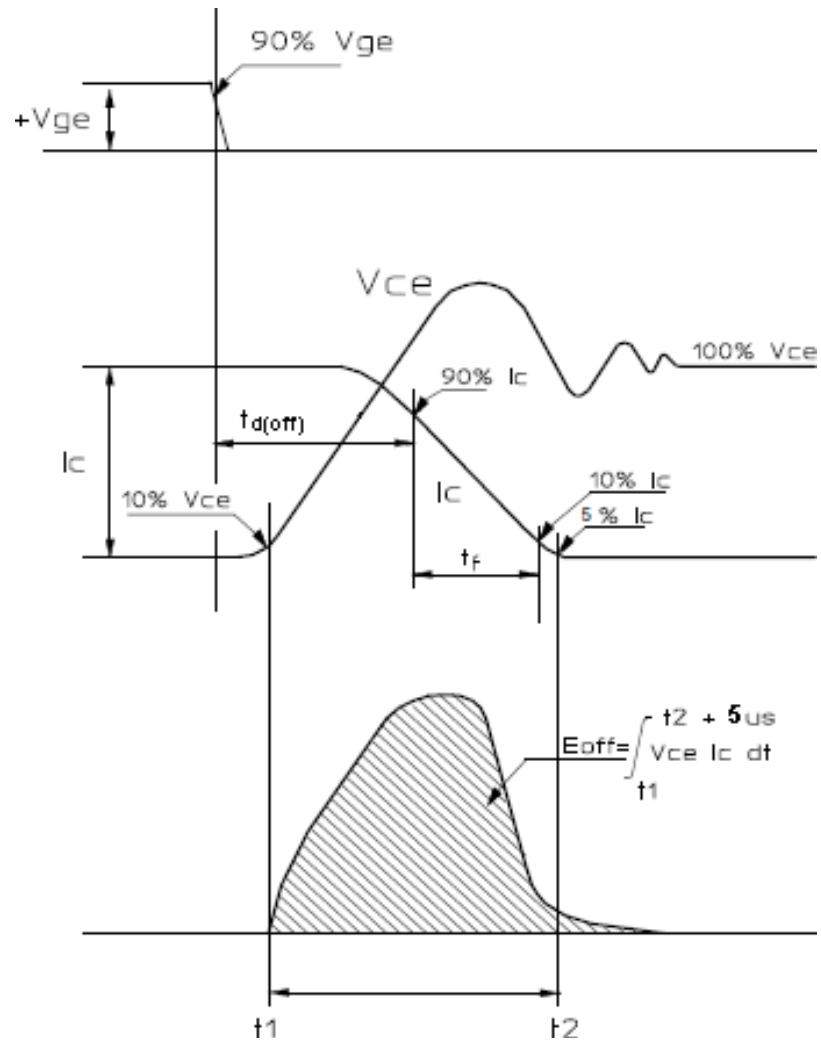
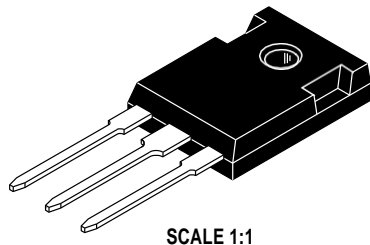
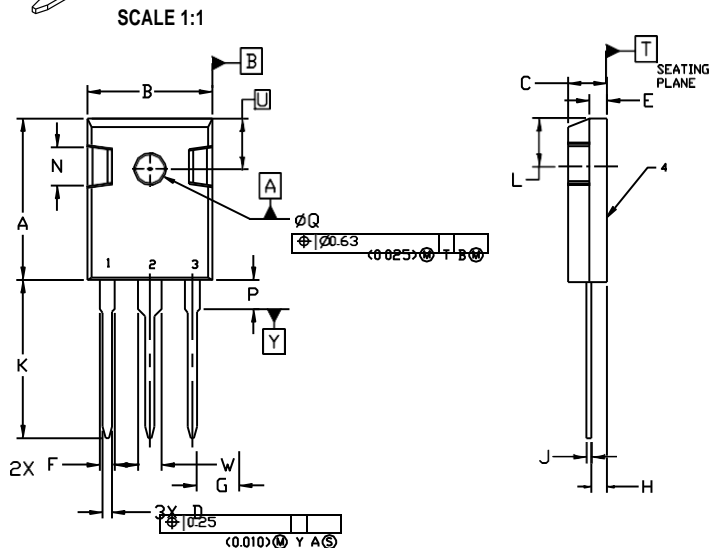


Figure 21. Definition of Turn Off Waveform



TO-247
CASE 340L
ISSUE G

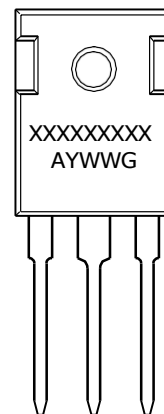
DATE 06 OCT 2021



NOTE 1: DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER

DIM	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	20.32	21.08	0.800	0.830
B	15.75	16.26	0.620	0.640
C	4.70	5.30	0.185	0.209
D	1.00	1.40	0.040	0.055
E	1.90	2.60	0.075	0.102
F	1.65	2.13	0.065	0.084
G	5.45	BSC	0.215	BSC
H	1.50	2.49	0.059	0.098
J	0.40	0.80	0.016	0.031
K	19.81	20.83	0.780	0.820
L	5.40	6.20	0.212	0.244
N	4.32	5.49	0.170	0.216
P	---	4.50	---	0.177
Q	3.55	3.65	0.140	0.144
U	6.15	BSC	0.242	BSC
W	2.87	3.12	0.113	0.123

GENERIC MARKING DIAGRAM*



- STYLE 1:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN
- STYLE 2:
PIN 1. ANODE
2. CATHODE (S)
3. ANODE 2
4. CATHODES (S)
- STYLE 3:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR
- STYLE 4:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR
- STYLE 5:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE
- STYLE 6:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. MAIN TERMINAL 2

- XXXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- WW = Work Week
- G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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